

Please replace the paragraph beginning at page 25, line 1 with the following new paragraph:

--Thereafter, an insulation film 28 not shown is formed, followed by a contact hole 29 formed on the insulating film. A transparent electrode such as ITO is electrically connected to the drain electrode 31. The above method realizes a liquid crystal display device that is capable of preventing incident light coming from upper and lower directions from reaching the TFT.--

IN THE CLAIMS:

Please amend claim 1 as follows.

1. (Amended) An active matrix liquid crystal display device comprising a liquid crystal cell, a switching element arranged in matrix, and shading layers mounted both on the upper side and the lower side of said switching element; wherein at least one of the upper and lower shading layers includes a sloped portion and has a convex shape disposed opposite to and protruding toward a gate electrode of said switching element.

Please add the following new claims 10-25.

--10. (New) The liquid crystal display device according to claim 2, wherein said upper shading layer and said lower shading layer are each formed of one of the following: a metal film (Al, Ta, Ti, W, Mo, Cr, Ni), a single layered film made of polysilicon and the like, AlSi, MoSi₂, TaSi₂, TiSi₂, WSi₂, CoSi₂, NiSi₂, PtSi, Pd₂S, HfN, ZrN, TiN, TaN, NbN, TiC, TaC or TiB₂, or of a structure formed by laminating said films.

11. (New) The liquid crystal display device according to claim 2, wherein either said upper shading layer or said lower shading layer or both said upper and lower shading layers is or are also used for wiring.

12. (New) A method for manufacturing the liquid crystal display device according to claim 2, wherein

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contd.*
the layer underneath either the upper shading layer or the lower shading layer is formed using SiO_2 , which is isotopically etched through HF using a resist mask, and removed of said mask before either the upper shading layer or the lower shading layer is formed thereon.

13. (New) A method for manufacturing the liquid crystal display device according to claim 2, wherein the layer underneath either the upper shading layer or the lower shading layer is formed using SiO_2 , which is isotopically dry-etched using a resist mask, and removed of said mask before either the upper shading layer or the lower shading layer is formed thereon.

14. (New) The liquid crystal display device according to claim 3, wherein said upper shading layer and said lower shading layer are each formed of one of the following: a metal film (Al, Ta, Ti, W, Mo, Cr, Ni), a single layered film made of

polysilicon and the like, AlSi, MoSi₂, TaSi₂, TiSi₂, WSi₂, CoSi₂, NiSi₂, PtSi, Pd₂S, HfN, ZrN, TiN, TaN, NbN, TiC, TaC or TiB₂, or of a structure formed by laminating said films.

15. (New) The liquid crystal display device according to claim 3, wherein either said upper shading layer or said lower shading layer or both said upper and lower shading layers is or are also used for wiring.

16. (New) A method for manufacturing the liquid crystal display device according to claim 3, wherein

the layer underneath either the upper shading layer or the lower shading layer is formed using SiO₂, which is isotopically etched through HF using a resist mask, and removed of said mask before either the upper shading layer or the lower shading layer is formed thereon.

17. (New) A method for manufacturing the liquid crystal display device according to claim 3, wherein the layer underneath either the upper shading layer or the lower shading layer is formed using SiO₂, which is isotopically dry-etched using a resist mask, and removed of said mask before either the upper shading layer or the lower shading layer is formed thereon.

18. (New) The liquid crystal display device according to claim 4, wherein said upper shading layer and said lower shading layer are each formed of one of the following: a metal film (Al, Ta, Ti, W, Mo, Cr, Ni), a single layered film made of

polysilicon and the like, AlSi, MoSi₂, TaSi₂, TiSi₂, WSi₂, CoSi₂, NiSi₂, PtSi, Pd₂S, HfN, ZrN, TiN, TaN, NbN, TiC, TaC or TiB₂, or of a structure formed by laminating said films.

19. (New) The liquid crystal display device according to claim 4, wherein either said upper shading layer or said lower shading layer or both said upper and lower shading layers is or are also used for wiring.

20. (New) A method for manufacturing the liquid crystal display device according to claim 4, wherein

the layer underneath either the upper shading layer or the lower shading layer is formed using SiO₂, which is isotopically etched through HF using a resist mask, and removed of said mask before either the upper shading layer or the lower shading layer is formed thereon.

21. (New) A method for manufacturing the liquid crystal display device according to claim 4, wherein the layer underneath either the upper shading layer or the lower shading layer is formed using SiO₂, which is isotopically dry-etched using a resist mask, and removed of said mask before either the upper shading layer or the lower shading layer is formed thereon.

22. (New) The liquid crystal display device according to claim 5, wherein said upper shading layer and said lower shading layer are each formed of one of the following: a metal film (Al, Ta, Ti, W, Mo, Cr, Ni), a single layered film made of

polysilicon and the like, AlSi, MoSi₂, TaSi₂, TiSi₂, WSi₂, CoSi₂, NiSi₂, PtSi, Pd₂S, HfN, ZrN, TiN, TaN, NbN, TiC, TaC or TiB₂, or of a structure formed by laminating said films.

23. (New) The liquid crystal display device according to claim 5, wherein either said upper shading layer or said lower shading layer or both said upper and lower shading layers is or are also used for wiring.

24. (New) A method for manufacturing the liquid crystal display device according to claim 5, wherein

the layer underneath either the upper shading layer or the lower shading layer is formed using SiO₂, which is isotopically etched through HF using a resist mask, and removed of said mask before either the upper shading layer or the lower shading layer is formed thereon.

25. (New) A method for manufacturing the liquid crystal display device according to claim 5, wherein the layer underneath either the upper shading layer or the lower shading layer is formed using SiO₂, which is isotopically dry-etched using a resist mask, and removed of said mask before either the upper shading layer or the lower shading layer is formed thereon.--
